

EGFM101-M THRU EGFM105-M

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EGFM101-M THRU EGFM105-M

1.0A Surface Mount Efficient Fast Rectifiers-50V~600V

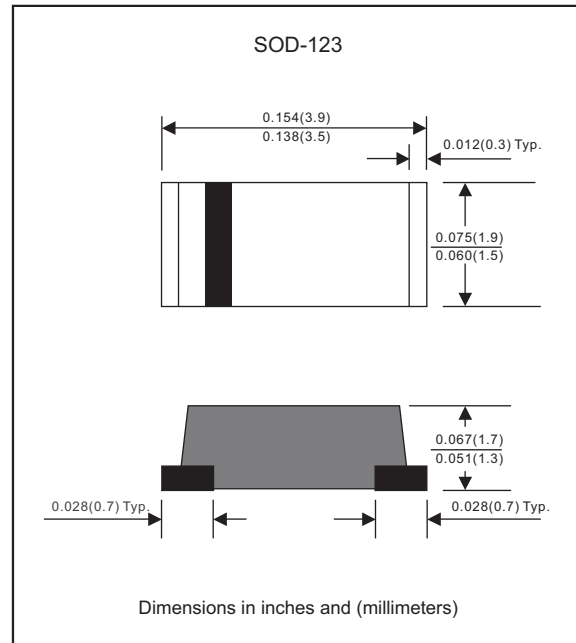
Features

- Batch process design, excellent power dissipation offers better reverse leakage current and thermal resistance
- Low profile surface mounted application in order to optimize board space
- High current & surge capability
- Low forward drop voltage
- Glass passivated chip junction
- Lead-free parts meet RoHS requirements
- Suffix "-H" indicates Halogen free parts, ex. EGFM101-M-H

Mechanical data

- Epoxy : UL94-V0 rated flame retardant
- Case : Molded plastic, SOD-123 / MINI SMA
- Terminals :Plated terminals, solderable per MIL-STD-750, Method 2026
- Polarity : Indicated by cathode band
- Mounting Position : Any
- Weight : Approximated 0.018 gram

Package outline



Maximum ratings (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOLS	EGFM101-M	EGFM102-M	EGFM103-M	EGFM104-M	EGFM105-M	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	V
Maximum continuous reverse voltage	V_R	50	100	200	400	600	V
Maximum average forward rectified current	I_o	1.0					A
Non-repetitive peak forward surge current 8.3ms single half sine-wave	I_{FSM}	20					A
Typical junction capacitance (Note 1)	C_J	15					pF
Operating junction temperature range	T_J	-55 to +150					$^{\circ}\text{C}$
Storage temperature range	T_{STG}	-65 to +175					$^{\circ}\text{C}$

Electrical characteristics (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOLS	EGFM101-M	EGFM102-M	EGFM103-M	EGFM104-M	EGFM105-M	UNIT
Maximum instantaneous forward voltage at $I_F=1.0\text{A}$	V_F	0.875			1.25	1.75	V
Maximum reverse leakage current $T_J=25^{\circ}\text{C}$ at rated V_R $T_J=125^{\circ}\text{C}$	I_R	5.0			100		μA
Maximum reverse recovery time (Note 2)	t_{rr}	25					ns

Thermal characteristics

PARAMETER	SYMBOLS	EGFM101-M	EGFM102-M	EGFM103-M	EGFM104-M	EGFM105-M	UNIT
Typical thermal resistance junction to ambient (Note 3)	$R_{\theta JA}$	54					$^{\circ}\text{C}/\text{W}$
Typical thermal resistance junction to case (Note 3)	$R_{\theta JC}$	39					$^{\circ}\text{C}/\text{W}$

Notes 1: Measured at 1 MHz and applied reverse voltage of 4.0 VDC
 2: Reverse recovery time test condition, $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{RR}=0.25\text{A}$
 3: Mounted on FR-4 PCB copper, minimum recommended pad layout

Rating and characteristic curves (EGFM101-M THRU EGFM105-M)

FIG.1-TYPICAL FORWARD CHARACTERISTICS

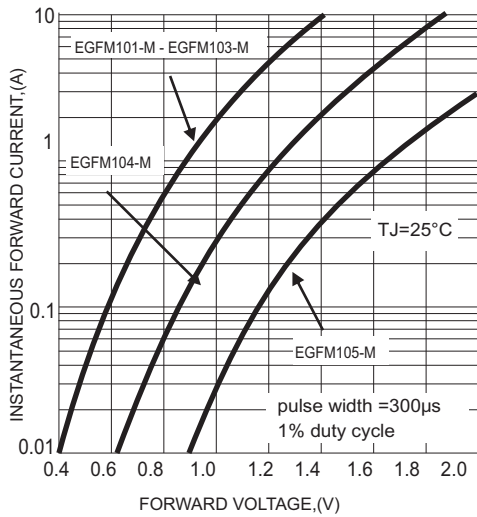


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

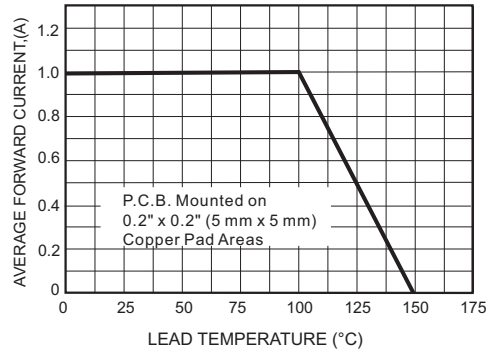
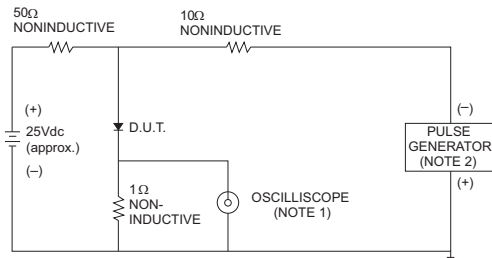


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



- NOTES: 1. Rise Time = 7ns max., Input Impedance = 1 megohm, 22pF.
2. Rise Time = 10ns max., Source Impedance = 50 ohms.

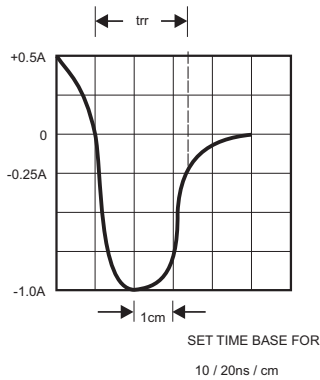


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

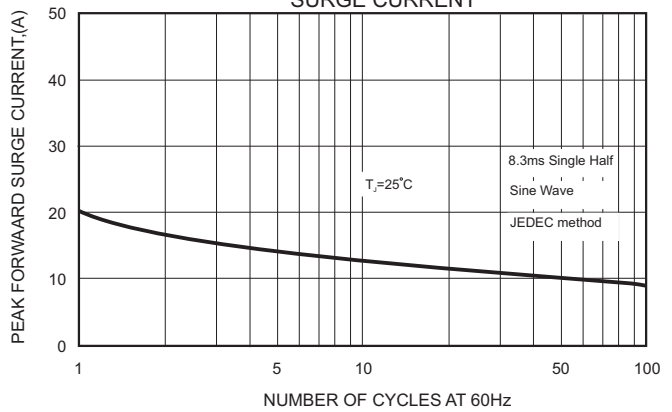
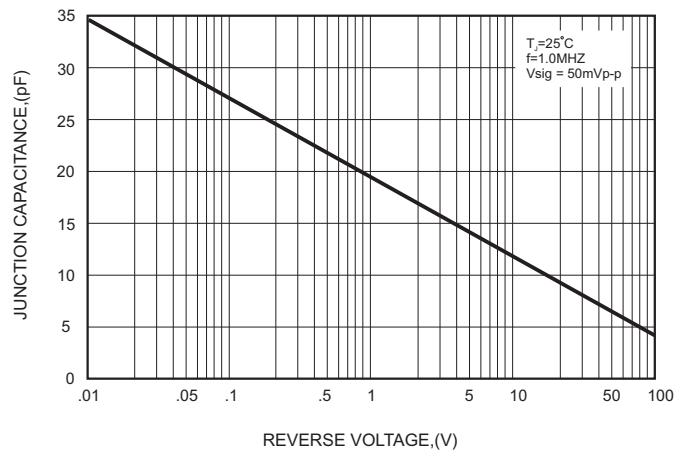




FIG.5-TYPICAL JUNCTION CAPACITANCE



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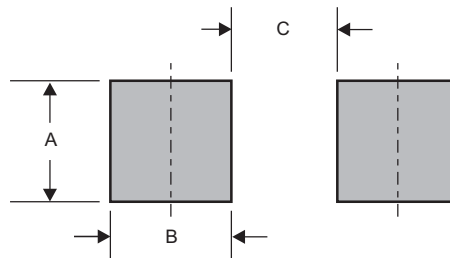
Pinning information

Pin	Simplified outline	Symbol
Pin1 cathode Pin2 anode		

Marking

Type number	Marking code
EGFM101-M	E1
EGFM102-M	E2
EGFM103-M	E3
EGFM104-M	E4
EGFM105-M	E5

Suggested solder pad layout

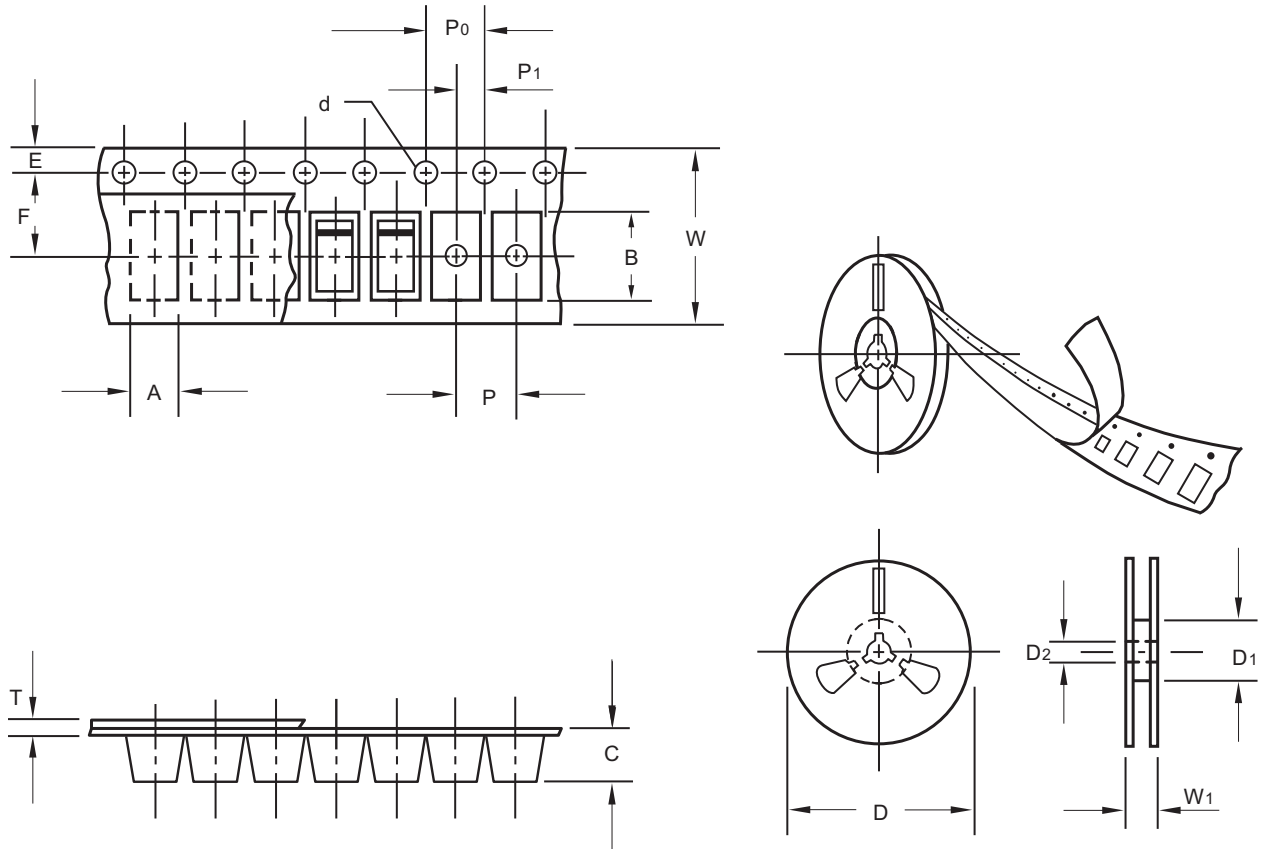


Dimensions in inches and (millimeters)

PACKAGE	A	B	C
SOD-123	0.075 (1.90)	0.055 (1.40)	0.075 (1.90)

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Packing information



unit:mm

Item	Symbol	Tolerance	SOD-123
Carrier width	A	0.1	1.90
Carrier length	B	0.1	3.90
Carrier depth	C	0.1	1.68
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D1	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	62.00
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W1	1.0	11.40

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

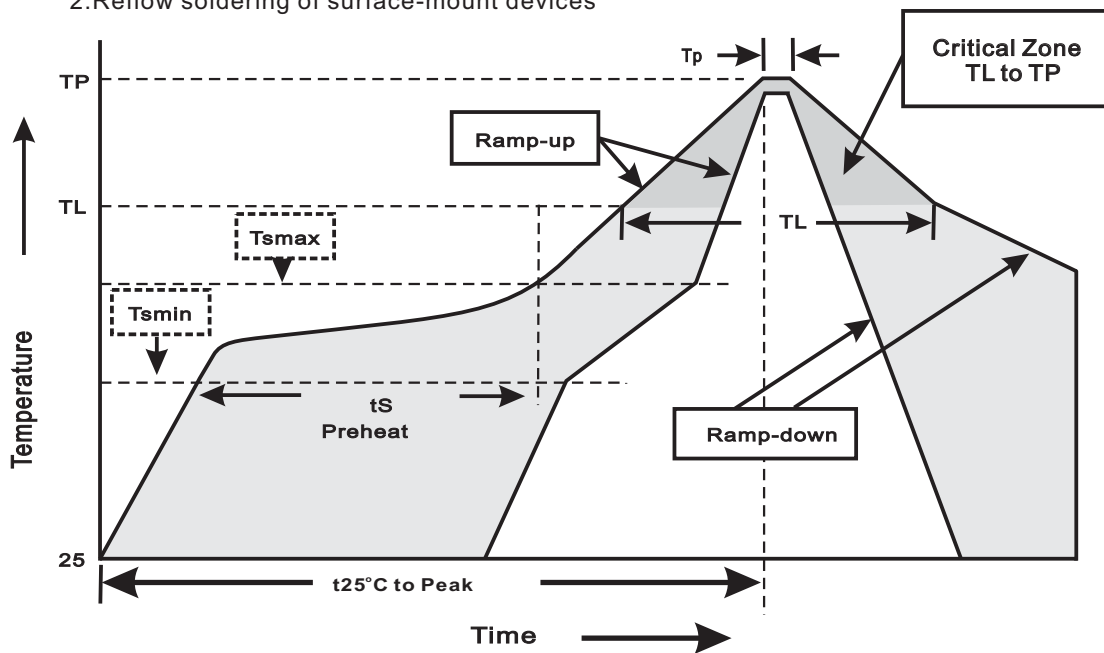
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Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOD-123	7"	2,500	4.0	25,000	183*183*123	178	382*262*387	200,000	10.5

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(T _L to T _P)	<3°C/sec
Preheat -Temperature Min(T _{smín}) -Temperature Max(T _{smáx}) -Time(min to max)(t _s)	150°C 200°C 60~120sec
T _{smáx} to T _L -Ramp-upRate	<3°C/sec
Time maintained above: -Temperature(T _L) -Time(t _L)	217°C 60~260sec
Peak Temperature(T _P)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(t _P)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes

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High reliability test capabilities

Item Test	Conditions	Reference
1. Solder Resistance	at 260±5°C for 10±2sec.	MIL-STD-750D METHOD-2031
2. Solderability	at 245±5°C for 5 sec.	MIL-STD-202F METHOD-208
3. High Temperature Reverse Bias	$V_R=80\%$ rate at $T_J=150^\circ\text{C}$ for 168 hrs.	MIL-STD-750D METHOD-1038
4. Forward Operation Life	Rated average rectifier current at $T_A=25^\circ\text{C}$ for 500hrs.	MIL-STD-750D METHOD-1027
5. Intermittent Operation Life	$T_A = 25^\circ\text{C}$, $I_F = I_O$ On state: power on for 5 min. off state: power off for 5 min. on and off for 500 cycles.	MIL-STD-750D METHOD-1036
6. Pressure Cooker	15P _{SIG} at $T_A=121^\circ\text{C}$ for 4 hrs.	JESD22-A102
7. Temperature Cycling	-55°C to +125°C dwelled for 30 min. and transferred for 5min. total 10 cycles.	MIL-STD-750D METHOD-1051
8. Forward Surge	8.3ms single half sine-wave , one surge.	MIL-STD-750D METHOD-4066-2
9. Humidity	at $T_A=85^\circ\text{C}$, RH=85% for 1000hrs.	MIL-STD-750D METHOD-1021
10. High Temperature Storage Life	at 175°C for 1000 hrs.	MIL-STD-750D METHOD-1031